



ZXTP25012EZ

20V PNP HIGH GAIN TRANSISTOR IN SOT89

Features

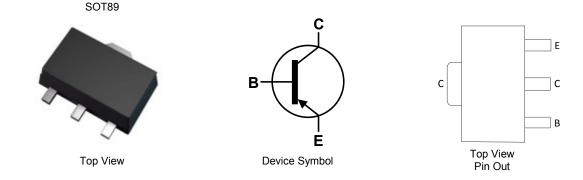
- BV_{CEO} > -12V
- I_C = -4.5A High Continuous Current
- Low Saturation Voltage V_{CE(sat)} < -70mV @ -1A
- $R_{sat} = 45m\Omega$ for a Low Equivalent On-Resistance
- P_D = 2.4W Power Dissipation
- Complementary part number ZXTN25012EZ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

Application

- High side switch
- Battery charging
- Regulator circuits
- Buck converters
- MOSFET gate drivers

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.05 grams (Approximate)



Ordering Information (Note 4)

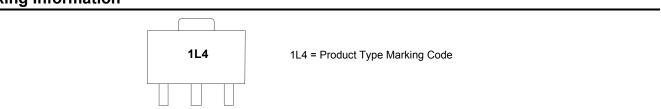
Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXTP25012EZTA	Standard	1L4	7	12	1,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-20	V
Collector-Emitter Voltage	VCEO	-12	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-4.5	A
Peak Pulse Collector Current (Single Pulse)	Ісм	-10	A
Base Current	IB	-1	A

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear Derating Factor	PD	1.1 8.8	W mW/°C
Power Dissipation (Note 6) Linear Derating Factor	PD	1.8 14.4	W mW/°C
Power Dissipation (Note 7) Linear Derating Factor	PD	2.4 19.2	W mW/°C
Power Dissipation (Note 8) Linear Derating Factor	PD	4.46 35.7	W mW/°C
Power Dissipation (Note 9) Linear Derating Factor	PD	19.2 153	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	117	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	68	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R _{0JA}	51	°C/W
Thermal Resistance, Junction to Ambient (Note 8)	R _{θJA}	28	°C/W
Thermal Resistance, Junction to Case (Note 9)	R _{eJC}	7.95	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	۵°

Notes: 5. For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; device measured when operating in steady state condition.

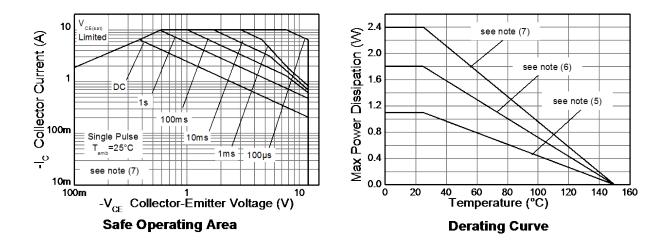
6. Same as note (5), except the device is mounted on 25mm x 25mm x 0.6mm single sided 1oz weight copper.
7. Same as note (5), except the device is mounted on 50mm x 50mm x 0.6mm single sided 1oz weight copper.

8. Same as note (5), except the device is measured at t<5 seconds.

9. Junction to case (collector tab). Typical.

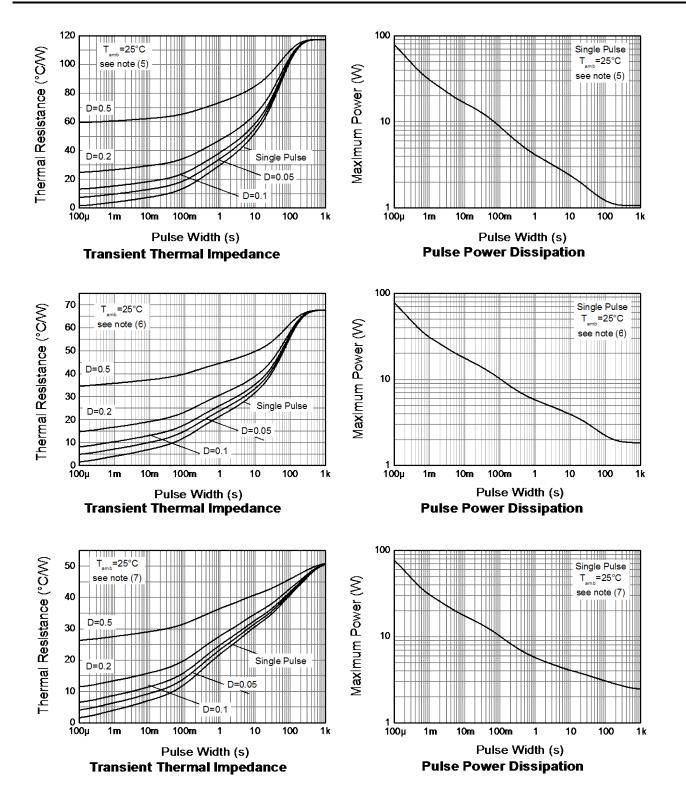


Thermal Characteristics and Derating Information





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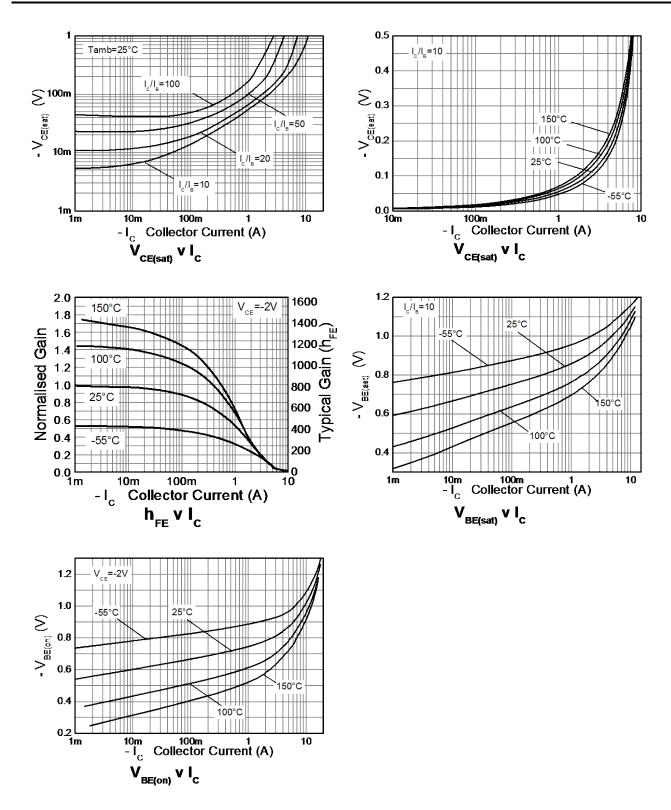
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-12	-35	_	V	I _C = -100μΑ
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-12	-25	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.5	_	V	I _E = -100μΑ
Collector Cut-Off Current	I _{CBO}	_	-1	-50 -0.5	nA μA	V _{CB} = -12V V _{CB} = -12V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	_	-1	-50	nA	V _{EB} = -5.6V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	_	-55 -155 -185 -200	-70 -265 -355 -285	mV	$I_{C} = -1A, I_{B} = -100mA$ $I_{C} = -1A, I_{B} = -10mA$ $I_{C} = -2A, I_{B} = -40mA$ $I_{C} = -5A, I_{B} = -450mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	_	-990	-1100	mV	I _C = -4.5A, I _B = -450mA
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	—	-865	-975	mV	I_{C} = -4.5A, V_{CE} = -2V
Static forward current transfer ratio (Note 10)	hFE	500 300 40 —	800 450 85 15	1500 — — —	_	$I_{C} = -10mA, V_{CE} = -2V$ $I_{C} = -1A, V_{CE} = -2V$ $I_{C} = -4.5A, V_{CE} = -2V$ $I_{C} = -10A, V_{CE} = -2V$
Transitional frequency	f _T	_	310		MHz	I _C = -50mA, V _{CE} = -10V, f = 100MHz
Input Capacitance	Ci _{bo}	—	127	250	pF	V _{EB} = -0.5V, f = 1MHz
Output Capacitance	C _{obo}	_	16.9	30	pF	V _{CB} = -10V, f = 1MHz
Delay time	t _d	_	41	—	ns	
Rise time	tr	_	62	_	ns	V _{CC} = -10V, I _C = -1A,
Storage time	ts	_	179	_	ns	$I_{B1} = -I_{B2} = -10mA$
Fall time	t _f		65		ns	

Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



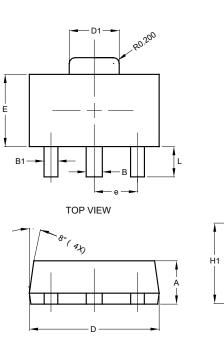
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

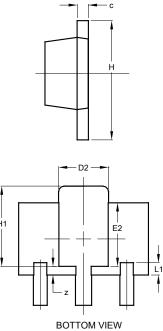




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.





SOT89

SOT89						
Dim	Min	Max	Тур			
Α	1.40	1.60	1.50			
В	0.50	0.62	0.56			
B1	0.42	0.54	0.48			
С	0.35	0.43	0.38			
D	4.40	4.60	4.50			
D1	1.62	1.83	1.733			
D2	1.61	1.81	1.71			
Е	2.40	2.60	2.50			
E2	2.05	2.35	2.20			
е	-	-	1.50			
Н	3.95	4.25	4.10			
H1	2.63	2.93	2.78			
L	0.90	1.20	1.05			
L1	0.327	0.527	0.427			
z	0.20	0.40	0.30			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89	

Dimensions	Value (in mm)
С	1.500
G	0.244
Х	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530



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